

BTA12, BTB12, T12xx

12 A Snubberless™, logic level and standard triacs

Features

- Medium current triac
- Low thermal resistance with clip bonding
- Low thermal resistance insulation ceramic for insulated BTA
- High commutation (4Q) or very high commutation (3Q) capability
- BTA series UL1557 certified (File ref: 81734)
- Packages are RoHS (2002/95/EC) compliant

Applications

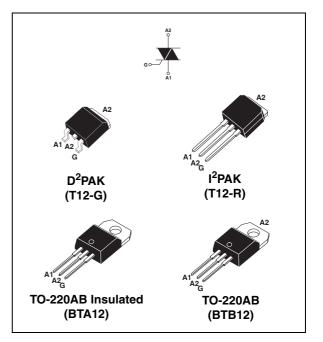
ON/OFF or phase angle function in applications such as static relays, light dimmers and appliance motors speed controllers.

The snubberless versions (BTA/BTB...W and T12 series) are especially recommended for use on inductive loads, because of their high commutation performances. The BTA series provides an insulated tab (rated at 2500 V RMS).

Description

Available either in through-hole or surface-mount packages, the **BTA12**, **BTB12** and **T12xx** triac series is suitable for general purpose mains power AC switching.

Device summary



Order code

See Ordering information on page 11

Symbol	Parameter	T12xx	BTA12 ⁽¹⁾	BTB12
I _{T(RMS)}	RMS on-state current	12	12	12
V _{DRM} /V _{RRM}	Repetitive peak off-state voltage	600/800	600/800	600/800
I _{GT} (Snubberless)	Triggering gate current	10/35/50	5/10/35/50	5/10/35/50
I _{GT} (Standard)	Triggering gate current	-	35/50	35/50

1. Insulated

Table 1.

TM: Snubberless is a trademark of STMicroelectronics

1 Characteristics

Symbol	Parame	eter		Value	Unit
I _{T(RMS)}	RMS on-state current (full sine wave)	I ² PAK / D ² PAK / TO-220AB	T _c = 105° C	12	A
. (TO-220AB Ins.	$T_c = 90^\circ C$		
	Non repetitive surge peak on-state F = 50 Hz		t = 20 ms	120	А
ITSM	current (full cycle, T_j initial = 25° C)	F = 60 Hz	t = 16.7 ms	126	A
l ² t	I ² t Value for fusing	t _p = 10 ms	78	A ² s	
dl/dt	Critical rate of rise of on-state current I_G = 2 x I_{GT} , t_r \leq 100 ns	F = 120 Hz	T _j = 125° C	50	A/µs
V _{DSM} /V _{RSM}	Non repetitive surge peak off-state voltage	t _p = 10 ms	$T_j = 25^\circ C$	V _{DRM} /V _{RRM} + 100	V
I _{GM}	Peak gate current	t _p = 20 μs	T _j = 125° C	4	А
P _{G(AV)}	Average gate power dissipation		T _j = 125° C	1	W
T _{stg} T _j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	°C

Table 2. Absolute maximum ratings

Table 3.Electrical characteristics ($T_j = 25^{\circ}C$, unless otherwise specified)Snubberless and logic level (3 quadrants)

Cumhal	Test conditions	Quedrant			T12xx		E	BTA12	BTB1	2	Unit
Symbol	rest conditions	Quadrant		T1210	T1235	T1250	тw	SW	CW	BW	Unit
I _{GT} ⁽¹⁾	V _D = 12 V	- -	MAX.	10	35	50	5	10	35	50	mA
V _{GT}	$R_L = 30 \Omega$	- -	MAX.			•	1.3				V
V _{GD}	$\begin{split} V_{D} &= V_{DRM} \\ R_{L} &= 3.3 \ \text{k}\Omega \\ T_{j} &= 125^{\circ} \ \text{C} \end{split}$	- -	MIN.	0.2			v				
I _H ⁽²⁾	l _T = 100 mA		MAX.	15	35	50	10	15	35	50	mA
١L		I - III	MAX.	25	50	70	10	25	50	70	mA
۱L	I _G = 1.2 I _{GT}	II		30	60	80	15	30	60	80	
dV/dt ⁽²⁾	$V_{D} = 67 \% V_{DRM}$ ga $T_{j} = 125^{\circ} C$	te open	MIN.	40	500	1000	20	40	500	1000	V/µs
	$(dV/dt)c = 0.1 V/\mu s$ T _j = 125° C			6.5			3.5	6.5			
(dl/dt)c ⁽²⁾	$(dV/dt)c = 10 V/\mu s$ T _j = 125° C		MIN.	2.9			1	2.9			A/ms
	Without snubber T _j = 125° C				6.5	12			6.5	12	

1. Minimum I_{GT} is guaranted at 5% of I_{GT} max

2. for both polarities of A2 referenced to A1



Symbol	Test Conditions	Quadrant		BTA12	BTB12	Unit	
Symbol	lest conditions	Quadrant		С	В	Unit	
I _{GT} ⁽¹⁾	$V_{\rm D} = 12 {\rm V} {\rm R}_{\rm L} = 30 {\Omega}$	- - V	MAX.	25 50	50 100	mA	
V _{GT}		ALL	MAX.	1.3		V	
V _{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_j = 125^{\circ} \text{ C}$	$3 \text{ k}\Omega \text{ T}_{j} = 125^{\circ} \text{ C}$ ALL		0.2		V	
I _H ⁽²⁾	I _T = 500 mA		MAX.	25	50	mA	
1	1 _ 1 2	I - III - IV	MAX.	40	50	mA	
١L	$I_{G} = 1.2 I_{GT}$	II	MAA.	80	100	ША	
dV/dt ⁽²⁾	$V_D = 67\% V_{DRM}$ gate open $T_j = 125^{\circ} C$		MIN.	200	400	V/µs	
(dV/dt)c ⁽²⁾	$(dI/dt)c = 5.3 \text{ A/ms}$ $T_j = 125^{\circ} \text{ C}$		MIN.	5	10	V/µs	

Table 4.Electrical characteristics ($T_j = 25^{\circ}C$, unless otherwise specified)
standard (4 quadrants)

1. Minimum I_{GT} is guaranted at 5% of I_{GT} max.

2. for both polarities of A2 referenced to A1.

Table 5. Static characteristics

Symbol	Test	Test conditions				
V _T ⁽¹⁾	$I_{TM} = 17 \text{ A}$ $t_p = 380 \ \mu \text{s}$	$T_j = 25^\circ C$	MAX.	1.55	V	
V _{t0} ⁽¹⁾	Threshold voltage	T _j = 125° C	MAX.	0.85	V	
R _d ⁽¹⁾	Dynamic resistance	T _j = 125° C	MAX.	35	mΩ	
I _{DRM}		$T_j = 25^\circ C$	MAX.	5	μA	
I _{RRM}	$V_{DRM} = V_{RRM}$	T _j = 125° C		1	mA	

1. for both polarities of A2 referenced to A1

Table 6.Thermal resistance

Symbol		Paramete	r	Value	Unit
D	lupation to appa (AC)		I ² PAK / D ² PAK / TO-220AB	1.4	°C/W
R _{th(j-c)} Junction to case (AC)		TO-220AB insulated	2.3	C/VV	
	Junction to ambient	$S^{(1)} = 1 \text{ cm}^2$	D ² PAK	45	
R _{th(j-a)}			TO-220AB / I ² PAK TO-220AB insulated	60	°C/W

1. Copper surface under tab.



Figure 1. Maximum power dissipation versus Figure 2. RMS on-state current (full cycle)

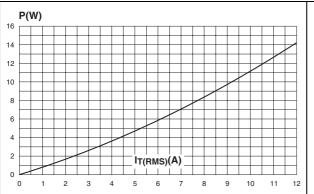


Figure 3. RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35µm) (full cycle)

temperature (full cycle)

RMS on-state current versus case

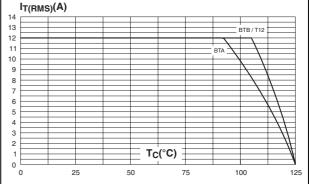


Figure 4. Relative variation of thermal impedance versus pulse duration

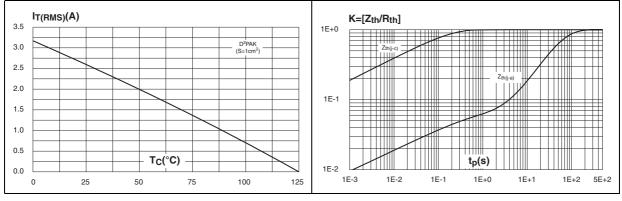
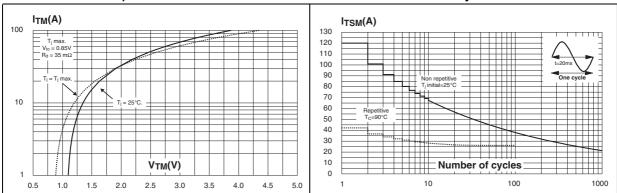


Figure 5. On-state characteristics (maximum Figure 6. values)

Surge peak on-state current versus number of cycles



- Figure 7. Non-repetitive surge peak on-state Figure 8. current for a sinusoidal pulse with width $t_p < 10$ ms and corresponding value of I^2t
- e 8. Figure 8: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values)

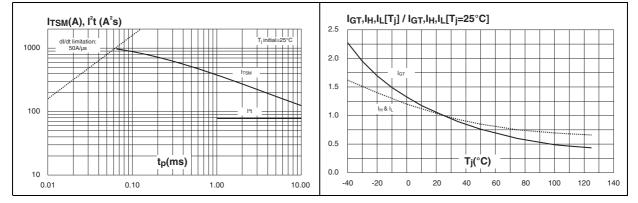
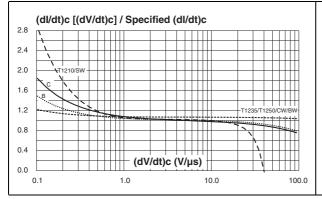
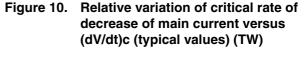


Figure 9. Relative variation of critical rate of I decrease of main current versus (dV/dt)c (typical values) (BW/CW/T1210/T1235)





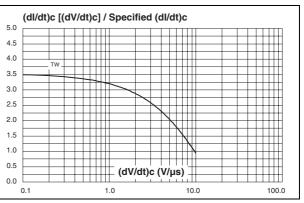
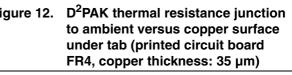
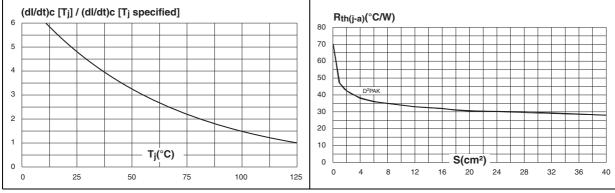


Figure 11. Relative variation of critical rate of Figure 12. decrease of main current versus junction temperature

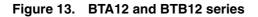
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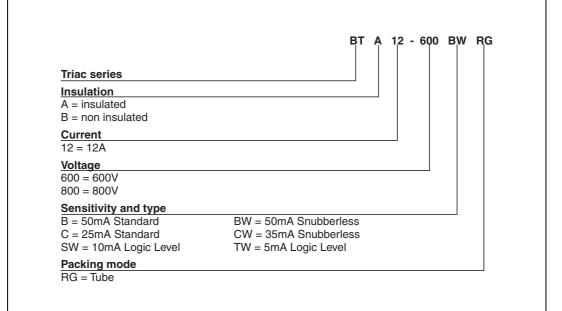




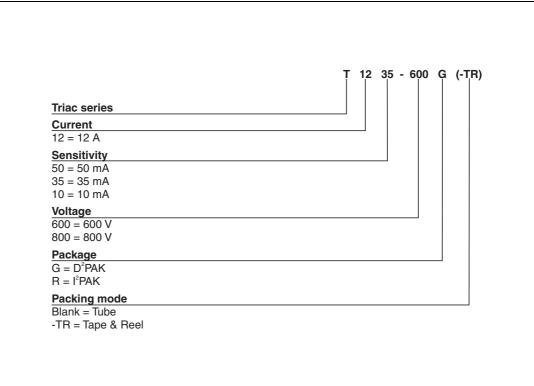
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2 Ordering information scheme











Order code ⁽¹⁾	Voltag	e (xxx)	Concitivity	Turne	Pookogo	
Order code	600 V	800 V	Sensitivity	Туре	Package	
BTA/BTB12-xxxBRG	Х	Х	50 mA	Standard	TO-220AB	
BTA/BTB12-xxxBWRG	Х	Х	50 mA	Snubberless	TO-220AB	
BTA/BTB12-xxxCRG	Х	Х	25 mA	Standard	TO-220AB	
BTA/BTB12-xxxCWRG	Х	Х	35 mA	Snubberless	TO-220AB	
BTA/BTB12-xxxSWRG	Х	Х	10 mA	Logic Level	TO-220AB	
BTA/BTB12-xxxTWRG	Х	Х	5 mA	Logic Level	TO-220AB	
T1210-800G	-	Х	10 mA	Logic Level	D ² PAK	
T1235-xxxG	Х	Х	35 mA	Snubberless	D ² PAK	
T1235-xxxR	Х	Х	35 mA	Snubberless	I ² PAK	
T1250-600G	Х	-	50 mA	Snubberless	D ² PAK	

Table 7.Product selector

1. BTB: non insulated TO-220AB package



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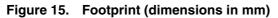
3 Packaging information

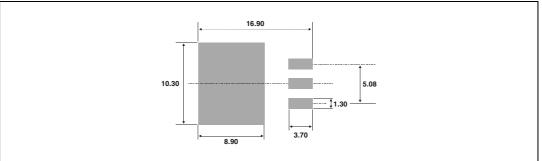
• Epoxy meets UL94, V0

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Table 8.D²PAK dimensions

					Dimer	nsions		
		Ref.	Mi	illimete	rs		Inches	
			Min.	Тур.	Max.	Min.	Тур.	Max.
		А	4.30		4.60	0.169		0.181
	← A→	A1	2.49		2.69	0.098		0.106
	C2→+←	A2	0.03		0.23	0.001		0.009
		В	0.70		0.93	0.027		0.037
L	C	B2	1.25	1.40		0.048	0.055	
		С	0.45		0.60	0.017		0.024
↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓		C2	1.21		1.36	0.047		0.054
→		D	8.95		9.35	0.352		0.368
G		Е	10.00		10.28	0.393		0.405
	2mm min.	G	4.88		5.28	0.192		0.208
		L	15.00		15.85	0.590		0.624
	V2	L2	1.27		1.40	0.050		0.055
		L3	1.40		1.75	0.055		0.069
		R		0.40			0.016	
		V2	0°		8°	0°		8°





					Dimer	nsions		
		Ref.	Mi	illimete	ers		Inches	
			Min.	Тур.	Max.	Min.	Тур.	Max.
	Α	А	4.30		4.60	0.169		0.181
, E ,		A1	2.49		2.69	0.098		0.106
		b	0.70		0.93	0.028		0.037
		b1	1.20		1.38	0.047		0.054
	D V4	b2	1.25	1.40		0.049	0.055	
	- V	с	0.45		0.60	0.018		0.024
↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓	A1 ,	c2	1.21		1.36	0.048		0.054
↓		D	8.95		9.35	0.352		0.368
L b1		е	2.44		2.64	0.096		0.104
		Е	10.00		10.28	0.394		0.405
	C	L	13.10		13.60	0.516		0.535
e		L1		3.75			0.148	
		L2	1.27		1.40	0.050		0.055
		۷		5°			5°	
		V4		45°			45°	

Table 9.I²PAK dimensions



					Dimer	nsions		
		Ref.	М	illimete	rs	Inches		
			Min.	Тур.	Max.	Min.	Тур.	Max.
		А	15.20		15.90	0.598		0.625
		a1		3.75			0.147	
	C C	a2	13.00		14.00	0.511		0.551
	b2,	В	10.00		10.40	0.393		0.409
	F	b1	0.61		0.88	0.024		0.034
A		b2	1.23		1.32	0.048		0.051
14 I3 ···.		С	4.40		4.60	0.173		0.181
	c2	c1	0.49		0.70	0.019		0.027
		c2	2.40		2.72	0.094		0.107
		е	2.40		2.70	0.094		0.106
	M	F	6.20		6.60	0.244		0.259
e → + + b1	←→ c1	ØI	3.75		3.85	0.147		0.151
		14	15.80	16.40	16.80	0.622	0.646	0.661
		L	2.65		2.95	0.104		0.116
		12	1.14		1.70	0.044		0.066
		13	1.14		1.70	0.044		0.066
		М		2.60			0.102	

 Table 10.
 TO-220AB dimensions (insulated and non-insulated)



4 Ordering information

Table 11.	Ordering inf	ormation
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Order code	Marking	Package	Weight	Base qty	Delivery mode	
BTA/BTB12-xxxyzRG	BTA/BTB12-xxxyz	TO-220AB	2.3 g	50	Tube	
T1210-xxxG-TR	T1210-xxxG	D ² PAK	1.5 g	1000	Tape and reel	
T1235-xxxG	T1235xxxG	D ² PAK	150	1.5 g	50	Tube
T1235-xxxG-TR	T1235xxxG	DFAN	1.5 g	1000	Tape and reel	
T1235-xxxR	T1235-xxxR	I ² PAK	1.5 g	50	Tube	
T1250-xxxG-TR	T1250xxxG	D ² PAK	1.5 g	1000	Tape and reel	

Note: xxx = voltage, y = sensitivity, z = type

5 Revision history

Table 12. Revision history

Date	Revision	Changes
Sep-2002	6A	Last update.
25-Mar-2005	7	 I²PAK package added. TO-220AB delivery mode changed from bulk to tube.
27-May-2005	8	T1210 added
28-Sep-2007	9	Reformatted to current standards. T1250 added

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